

PROTECTION PRODUCTS - MicroClamp[™] Description

The μ ClampTM series of TVS arrays are designed to protect sensitive electronics from damage or latch-up due to ESD, lightning, and other voltage-induced transient events. Each device will protect up to four lines operating at **3.3 volts**.

The µClamp[™]3305P is a solid-state device designed specifically for transient suppression. It is constructed using Semtech's proprietary EPD process technology. The EPD process provides low standoff voltages with significant reductions in leakage currents and capacitance over traditional pn junction processes. They offer desirable characteristics for board level protection including fast response time, low clamping voltage and no device degradation.

The μ Clamp3305P may be used to meet the immunity requirements of IEC 61000-4-2, level 4 (±15kV air, ±8kV contact discharge). It is packaged in an ultra small SLP1616P6 package with a low profile of only 0.58mm. The leads are spaced at a pitch of 0.5mm and are finished with lead-free NiPdAu. The small package makes it ideal for use in portable electronics such as cell phones, digital still cameras, and notebook computers.

Features

- Transient protection for data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (tp = 5/50ns)
- Small package for use in portable electronics
- Protects five I/O lines
- Working voltage: 3.3V
- Low leakage current
- Low operating and clamping voltages
- Solid-state silicon-avalanche technology

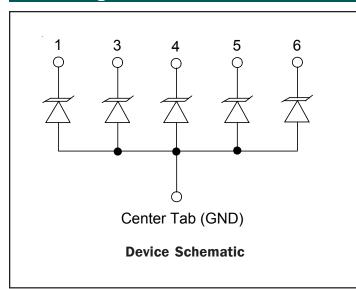
Mechanical Characteristics

- SLP1616P6 package
- RoHS/WEEE Compliant
- Nominal Dimensions: 1.6 x 1.6 x 0.58 mm
- Lead Pitch: 0.5mm
- Lead Finish: NiPdAu
- Marking : Orientation Mark and Marking Code
- Packaging : Tape and Reel

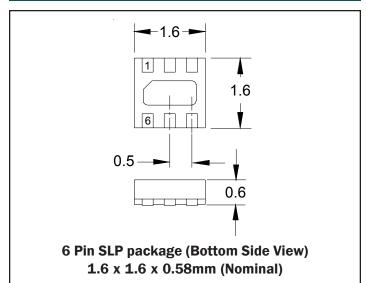
Applications

- Cellular handsets and accessories
- Notebooks and handhelds
- MP3 Players
- Digital cameras
- Portable instrumentation
- PDA's

Circuit Diagram



Package



uClamp3305P

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PROTECTION PRODUCTS

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (tp = 8/20µs)	P _{pk}	40	Watts
Maximum Peak Pulse Current (tp = 8/20µs)	l _{pp}	5	Amps
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{pp}	+/- 20 +/- 15	kV
Operating Temperature	T,	-55 to +125	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics (T=25°C)

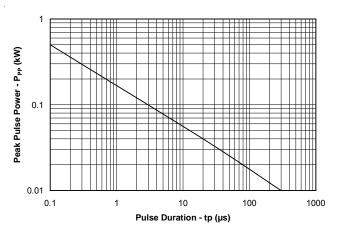
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Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V _{RWM}				3.3	V
Punch-Through Voltage	V _{PT}	Ι _{ρτ} = 2μΑ	3.5	3.9	4.6	V
Snap-Back Voltage	V _{SB}	I _{se} = 50mA	2.8			V
Reverse Leakage Current	I _R	V _{RWM} = 3.3V		0.05	0.5	μA
Clamping Voltage	V _c	I _{PP} = 1A, tp = 8/20µs Any I/O to Gnd			5.5	V
Clamping Voltage	V _c	I _{PP} = 5A, tp = 8/20µs Any I/O to Gnd			8.0	V
Reverse Clamping Voltage	V _{CR}	I _{pp} = 1A, tp = 8/20µs Any I/O to Gnd			2.4	V
Junction Capacitance	C _j	I/O pin to Gnd V _R = OV, f = 1MHz		20	25	pF
		I/O pin to Gnd V _R = 3.3V, f = 1MHz		12		pF
		I/O pin to I/O pin V _R = OV, f = 1MHz		10	12.5	pF
		I/O pin to I/O pi n V _R = 3.3V, f = 1MHz		7.5		pF

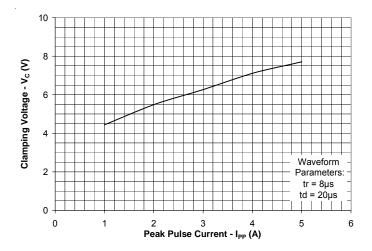


Typical Characteristics

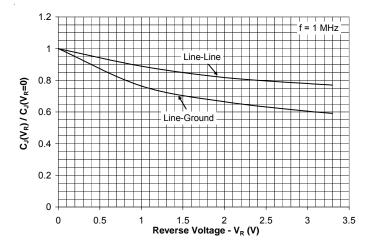
Non-Repetitive Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

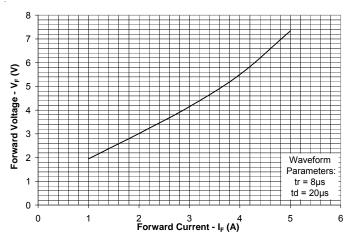


Normalized Capacitance vs. Reverse Voltage

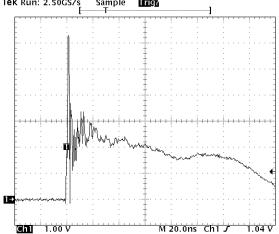


Power Derating Curve 110 100 90 % of Rated Power or I_{PP} 80 70 60 50 40 30 20 10 0 0 25 100 125 150 50 75 Ambient Temperature - T_A (°C)

Forward Voltage vs. Forward Current



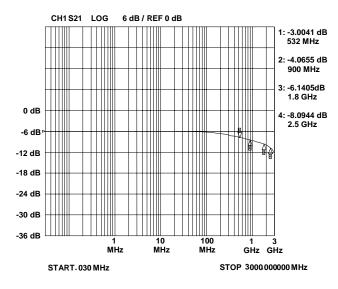
ESD Clamping (8kV Contact per IEC 61000-4-2) Tek Run: 2.50GS/s sample



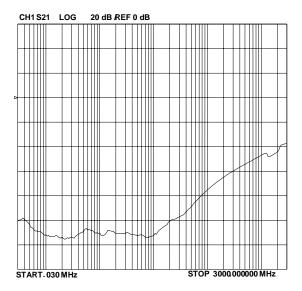
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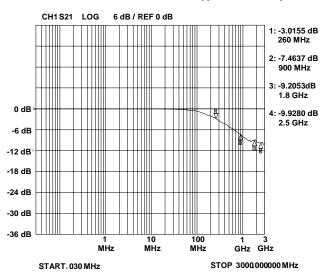
Insertion Loss S21 - LtoL (I/O to I/O)



Crosstalk S21 (I/O to Pin 4)



Insertion Loss S21 -LtoG (I/O to Pin 2)





Applications Information

Device Connection Options

The μ Clamp3305P is designed to protect 5 signal lines with an operating voltage of 0 to 3.3V. It will present a high impedance to the protected line up to 3.3 volts. It will "turn on" when the line voltage exceeds 3.5 volts. The device is unidirectional and may be used on lines where the signal polarity is above ground.

Pin 1,3,4,5,6 are connected to I/O signals. The center tab is connected to system ground. Pin 2 should be left open or not connected. All signal lines and ground should be made with the lowest impedance and inductance path as possible. This will improve signal quality of the lines and keep the clamping voltage as low as possible during a fast transient.

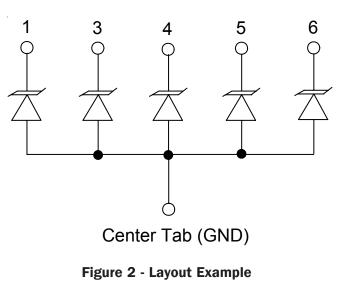
Due to the "snap-back" characteristics of the low voltage TVS, it is not recommended that the I/O line be directly connected to a DC source greater than snap-back voltage (V_{SR}) as the device can latch on.

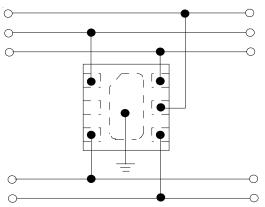
EPD TVS Characteristics

These devices are constructed using Semtech's proprietary EPD technology. The structure of the EPD TVS is vastly different from the traditional pn-junction devices. At voltages below 5V, high leakage current and junction capacitance render conventional avalanche technology impractical for most applications. However, by utilizing the EPD technology, these devices can effectively operate at 3.3V while maintaining excellent electrical characteristics.

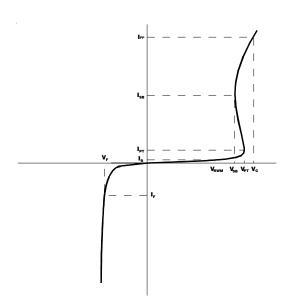
The EPD TVS employs a complex nppn structure in contrast to the pn structure normally found in traditional silicon-avalanche TVS diodes. The EPD mechanism is achieved by engineering the center region of the device such that the reverse biased junction does not avalanche, but will "punch-through" to a conducting state. This structure results in a device with superior DC electrical parameters at low voltages while maintaining the capability to absorb high transient currents.

Figure 1 - Circuit Diagram





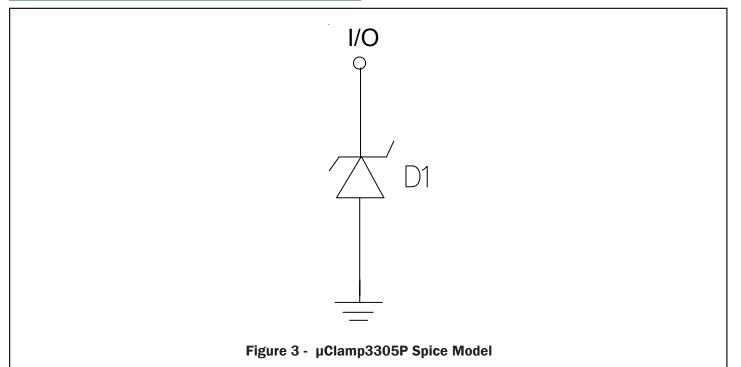






PROTECTION PRODUCTS - MicroClamp™

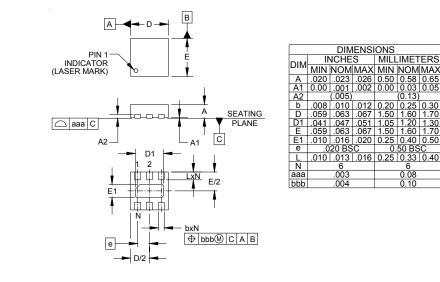
Applications Information - Spice Model



µClamp3305P Spice Parameters							
Parameter	Unit	D1 (TVS)					
IS	Amp	2E-12					
BV	Volt	20					
VJ	Volt	0.57					
RS	Ohm	1.444					
IBV	Amp	1.0 E-3					
CJO	Farad	20E-12					
TT	sec	2.541E-9					
М		0.236					
N		1.1					
EG	eV	1.11					



Outline Drawing - SLP1616P6

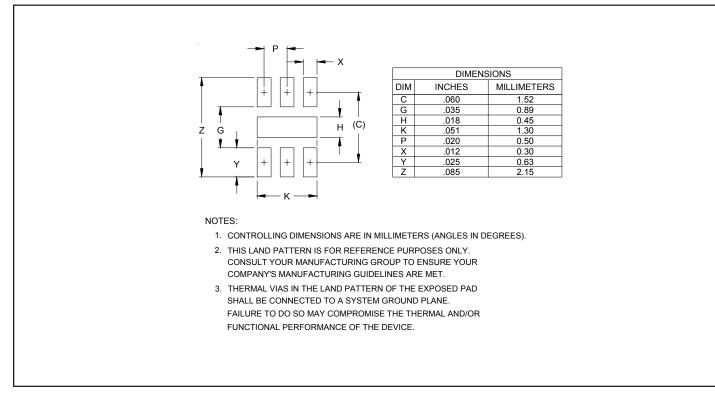




- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

6 0.08 0.10

Land Pattern - SLP1616P6







Marking



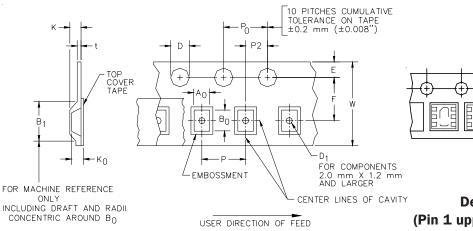
Ordering Information

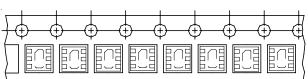
Part Number	Working	Lead	Qty per	Reel	
	Voltage	Finish	Reel	Size	
uClamp3305P.TCT	3.3V	Pb Free	3,000	7 Inch	

MicroClamp, uClamp and $\mu Clamp$ are marks of Semtech Corporation

Y = year W = Week

Tape and Reel Specification





Device Orientation in Tape (Pin 1 upper left towards sprocket holes)

	A0	В0		ко							
1.78 +/-	-0.10 mm	1.78 +/-0.10	mm ().69 +/-0.10 mm	1						
Tape Width	B, (Max)	D	D1	E	F	K (MAX)	Р	PO	P2	T(MAX)	w
8 mm	4.2 mm (.165)	1.5 + 0.1 mm - 0.0 mm (0.59 +.005 000)	0.8 mm ±0.05 (.031)	1.750±.10 mm (.069±.004)	3.5±0.05 mm (.138±.002)	2.4 mm (.094)	4.0±0.1 mm (.157±.00- 4)	4.0±0.1 mm (.157±.00- 4)	2.0±0.05m- m (.079±.002)	0.4 mm (.016)	8.0 mm + 0.3 mm - 0.1 mm (.312±.012)

Contact Information

Semtech Corporation Protection Products Division 200 Flynn Rd., Camarillo, CA 93012 Phone: (805)498-2111 FAX (805)498-3804

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